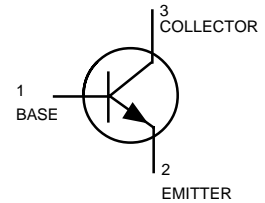
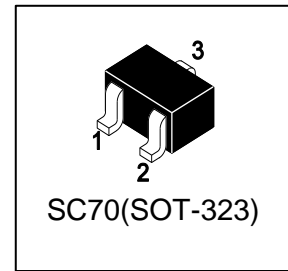


# LBC846BWT1G

## S-LBC846BWT1G

General Purpose Transistors NPN Silicon



### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

### 2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBC846BWT1G	1B	3000/Tape&Reel

### 3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	65	V
Collector–Base Voltage	V <sub>CBO</sub>	80	V
Emitter–Base Voltage	V <sub>EB0</sub>	6	V
Collector Current — Continuous	I <sub>C</sub>	100	mA

### 4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation,	PD	150	mW
Thermal Resistance, Junction–to–Ambient	R <sub>θJA</sub>	833	°C/W
Junction and Storage temperature	T <sub>J</sub> , T <sub>stg</sub>	-55~+150	°C

## 5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

### OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = 10 mA, IB = 0)	VBR(CEO)	65	-	-	V
Collector–Emitter Breakdown Voltage (IC = 10 μA, VEB = 0)	VBR(CES)	80	-	-	V
Collector–Base Breakdown Voltage (IC = 10 μA, IE= 0)	VBR(CBO)	80	-	-	V
Emitter–Base Breakdown Voltage (IE = 1.0 μA, IC = 0)	VBR(EBO)	6	-	-	V
Collector Cutoff Current (VCB = 30 V) (VCB = 30 V, TA = 150°C)	ICBO	-	-	15 5	nA μA
Collector-Emitter cutoff Current (VCE=65V, IB=0)	ICEO	-	-	10	μA
Emitter-Base cut-off current (VBE =6V,IC =0)	IEBO	-	-	100	nA

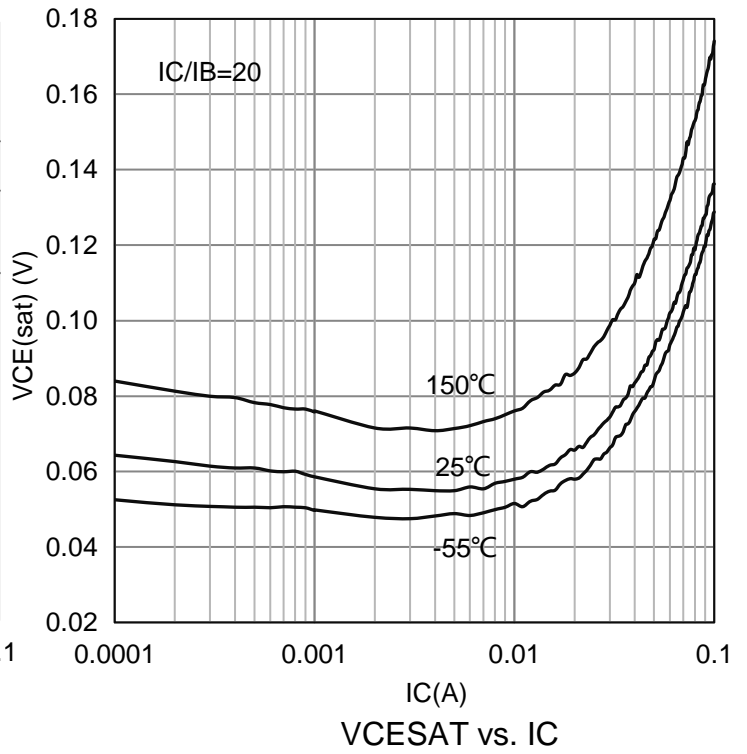
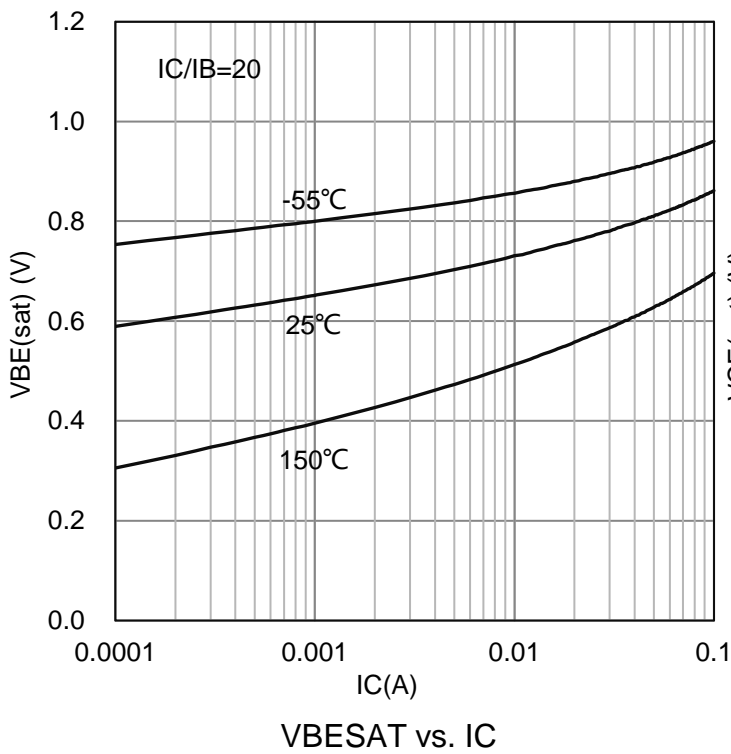
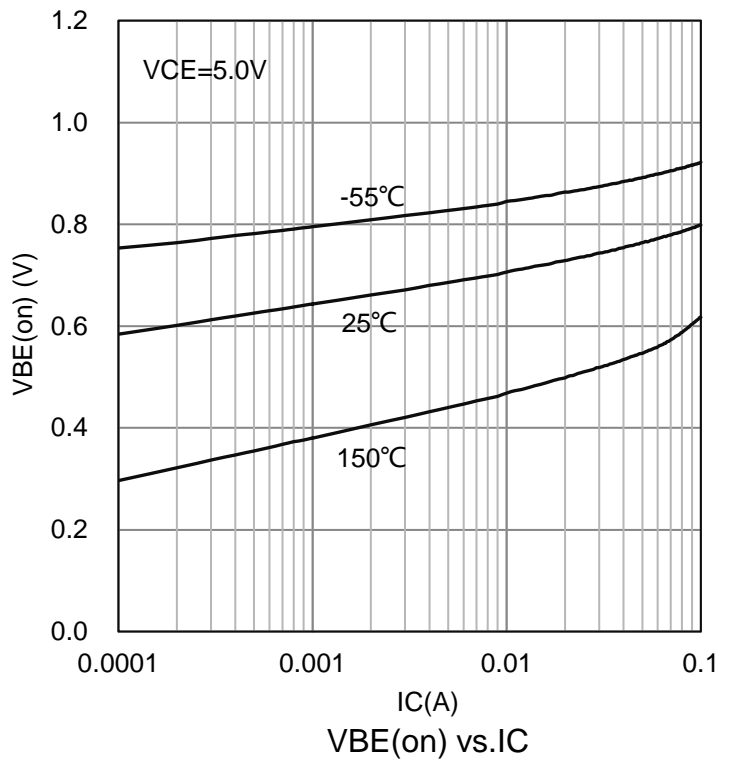
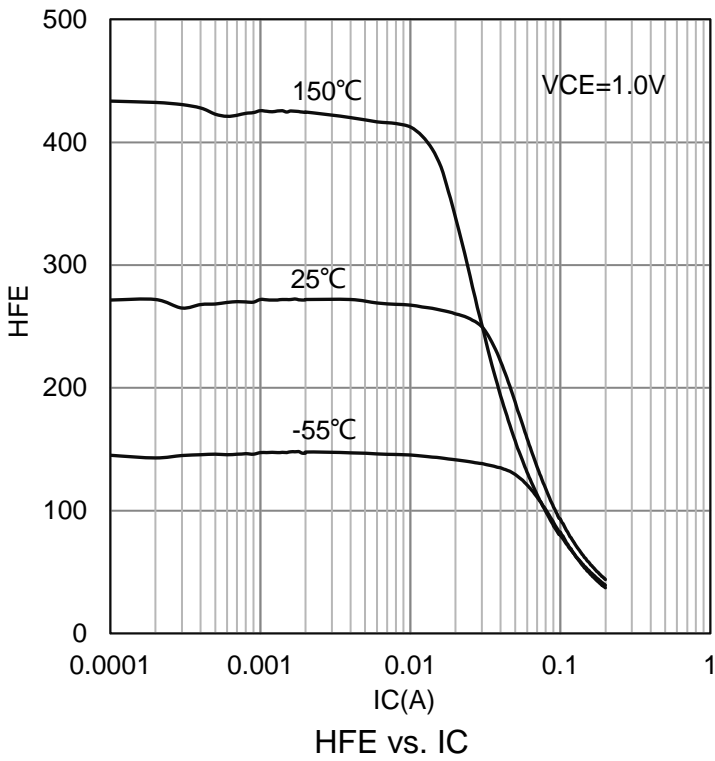
### ON CHARACTERISTICS

DC Current Gain (IC = 2.0 mA, VCE = 5.0 V)	HFE	200	290	450	
Collector–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VCE(sat)	-	-	0.25 0.6	V
Base–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VBE(sat)	-	0.7 0.9	-	V
Base–Emitter turn on Voltage (IC = 2.0 mA, VCE = 5.0 V) (IC = 10 mA, VCE = 5.0 V)	VBE(on)	580	660	700 770	mV

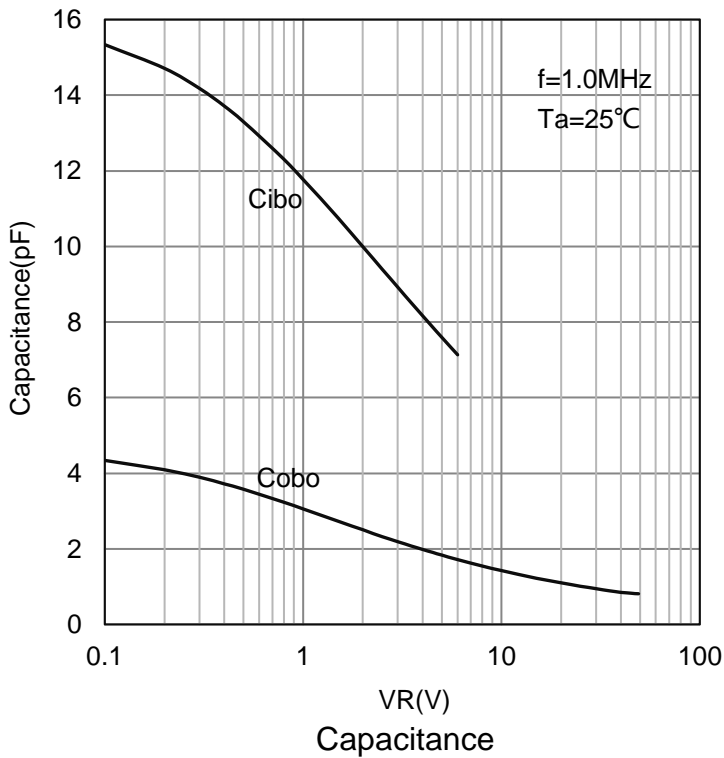
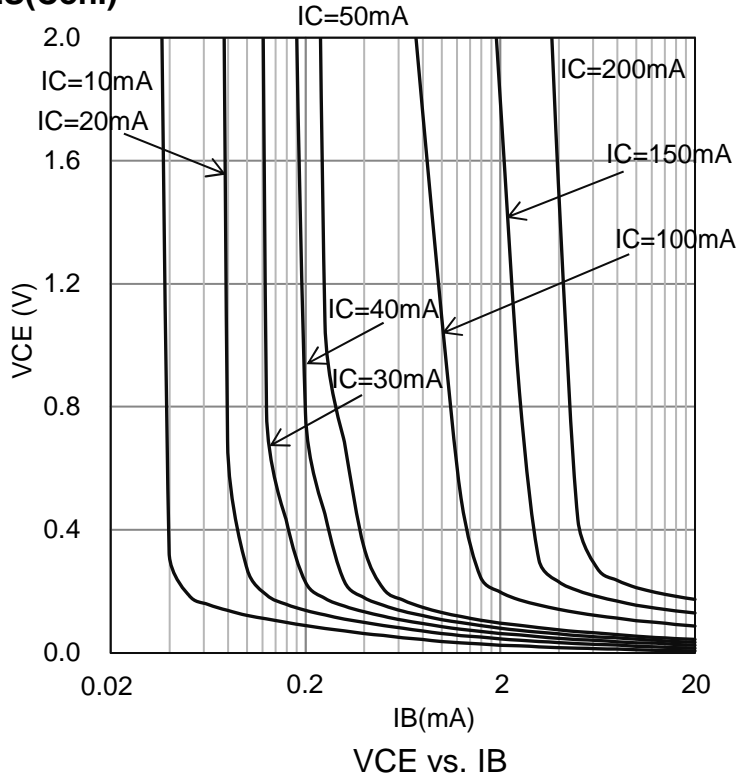
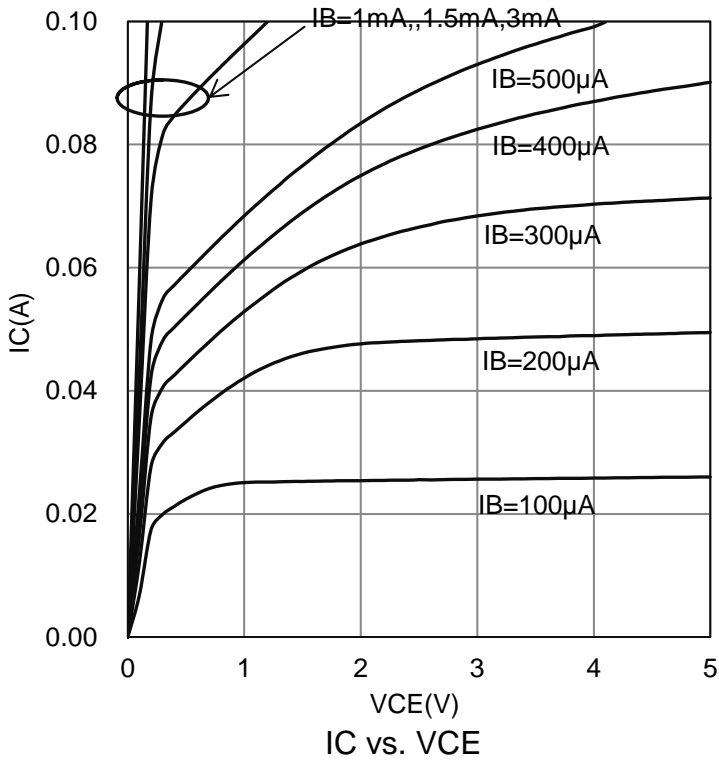
### SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (IC = 10 mA, VCE = 5.0 V, f = 100 MHz)	fT	100	-	-	MHz
Output Capacitance (VCB = 10 V, f = 1.0 MHz)	Cobo	-	-	4.5	pF
Noise Figure (IC = 0.2 mA, VCE = 5.0 V, RS = 2.0 kΩ f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB

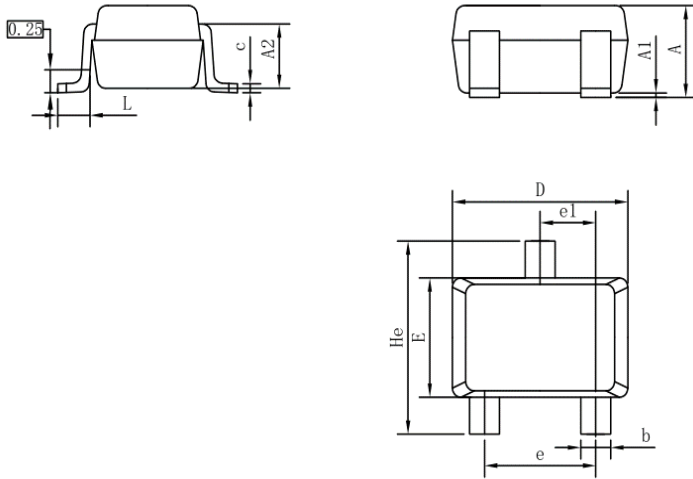
**6.ELECTRICAL CHARACTERISTICS CURVES**



**6.ELECTRICAL CHARACTERISTICS CURVES(Con.)**

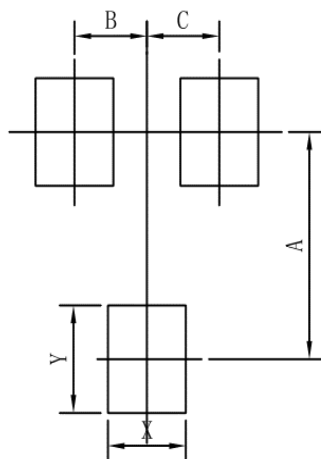


### 7. OUTLINE AND DIMENSIONS



SC70			
DIM	MIN	NOR	MAX
A	0.80	0.95	1.00
A1	0.00	0.05	0.10
A2	0.7 REF		
b	0.30	0.35	0.40
c	0.10	0.15	0.25
D	1.80	2.05	2.20
E	1.15	1.30	1.35
e	1.20	1.30	1.40
e1	0.65 BSC		
L	0.20	0.35	0.56
He	2.00	2.10	2.40
ALL Dimension in mm			

### 8. SOLDERING FOOTPRINT



SC70	
DIM	MIN
A	1.90
B	0.65
C	0.65
X	0.70
Y	0.90

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)